

### Characterization of irradiated SiPM for the TOP detector at the Belle II experiment

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#### Content

#### Done:

- Fit gain as function of bias voltage and extract breakdown voltage for low irradiated modules
- Darkcount rates for low irradiated modules
- Time resolutions for low irradiated modules

#### To Do:

- Extract breakdown voltage for highly irradiated modules
- Check time resolution of highly irradiated modules



### Tests with irradiated modules in Padova



- In Belle II, MCP-PMTs with extended lifetime have been installed and they have limited lifetime depending on accumulated charge.
- We are trying to understand if they eventually can be replaced with SiPMs.
- We irradiated 24 SiPMs modules with different neutron fluxes and tested by laser.
- Sixteen of them are processed to study their response.
- Collected data are read from modules and analyzed.

Index	Producer	Dimension	Pitch	Neutron $1 \text{ MeV}$
		$[mm \times mm]$	$[\mu \mathrm{m}]$	$\rm eg/cm^2$ fluence
0	Hamamatsu	$1.3 \times 1.3$	50	$5.0 \cdot 10^{11}$
1	Hamamatsu	$1.3 \times 1.3$	50	$2.0 \cdot 10^{11}$
2	Hamamatsu	$1.3 \times 1.3$	50	$1.0 \cdot 10^{11}$
3	Hamamatsu	$1.3 \times 1.3$	50	$5.0 \cdot 10^{10}$
4	Hamamatsu	$1.3 \times 1.3$	50	$2.0 \cdot 10^{10}$
5	Hamamatsu	$1.3 \times 1.3$	50	$1.0 \cdot 10^{10}$
6	Hamamatsu	$1.3 \times 1.3$	50	$5.0{\cdot}10^9$
7	Hamamatsu	$1.3 \times 1.3$	50	$1.0 \cdot 10^{9}$



# SiMP #0



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Gain as function of bias voltage for SiPM #0 irradiated at level 5.0 · 10<sup>11</sup> at 10 °C





Gain as function of bias voltage for SiPM #0 irradiated at level 5.0 · 10<sup>11</sup> at -10 °C





Gain as function of bias voltage for SiPM #0 irradiated at level 5.0 · 10<sup>11</sup> at -30 °C





























## SiMP #1



Gain as function of bias voltage for SiPM #1 irradiated at level 2.0 · 10<sup>11</sup> at 10 °C





Gain as function of bias voltage for SiPM #1 irradiated at level 2.0 · 10<sup>11</sup> at -10 °C



































# SiMP #2



Gain as function of bias voltage for SiPM #2 irradiated at level 1.0 · 10<sup>11</sup> at 10 °C





Gain as function of bias voltage for SiPM #2 irradiated at level 1.0 · 10<sup>11</sup> at -10 °C







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# SiMP #3



Gain as function of bias voltage for SiPM #3 irradiated at level 5.0 · 10<sup>10</sup> at 10 °C





Gain as function of bias voltage for SiPM #3 irradiated at level 5.0 · 10<sup>10</sup> at -10 °C






0.5

0.4

0.3

0.2

0.1

0.5

0.4

0.3

0.2

0.1

Time resolution [ns]

Time resolution [ns]



 $V_{bias} - V_0 [V]$ 

 $V_{bias} - V_0 [V]$ 

Jakub Kandra, INFN Padova V<sub>bias</sub> - V<sub>0</sub> [V]























# SiMP #4



Gain as function of bias voltage for SiPM #4 irradiated at level 2.0 · 10<sup>10</sup> at 10 °C





Gain as function of bias voltage for SiPM #4 irradiated at level 2.0 · 10<sup>10</sup> at -10 °C





Gain as function of bias voltage for SiPM #4 irradiated at level 2.0 · 10<sup>10</sup> at -30 °C









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# SiMP #5



Gain as function of bias voltage for SiPM #5 irradiated at level  $1.0 \cdot 10^{10}$  at  $10^{\circ}$ C





Gain as function of bias voltage for SiPM #5 irradiated at level 1.0 · 10<sup>10</sup> at -10 °C





Gain as function of bias voltage for SiPM #5 irradiated at level 1.0 · 10<sup>10</sup> at -30 °C





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# SiMP #6



Gain as function of bias voltage for SiPM #6 irradiated at level  $5.0 \cdot 10^9$  at 10 °C





Gain as function of bias voltage for SiPM #6 irradiated at level 5.0 · 10<sup>9</sup> at -10 °C





Gain as function of bias voltage for SiPM #6 irradiated at level 5.0 · 10<sup>9</sup> at -30 °C




























# SiMP #7

## Gain as function of bias voltage for



Gain as function of bias voltage for SiPM #7 irradiated at level 1.0 · 10<sup>9</sup> at 10 °C



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# Gain as function of bias voltage for

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Gain as function of bias voltage for SiPM #7 irradiated at level 1.0 · 10<sup>9</sup> at -10 °C



#### Gain as function of bias voltage for



Gain as function of bias voltage for SiPM #7 irradiated at level 1.0 · 10<sup>9</sup> at -30 °C



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# **Time resolution**





# **Time resolution**





# **Time resolution**



















# Backup

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# Breakdown voltages at temperatures for SiPMs



Index of SiPM		0	1	2	3	4	5	6	7
Producer		Hamamatsu							
Dimension [mm×mm]		1.3  imes 1.3	$1.3 \times 1.3$						
Pitch $[\mu m]$		50	50	50	50	50	50	50	50
Temperature		Breakdown							
$[^{\circ}C]$	Status	voltage $[V_0]$							
20	No-irradiated	$51.6 \pm 0.2$	$51.4 \pm 0.2$	$51.1 \pm 0.2$	$51.3 \pm 0.2$	$51.1 \pm 0.2$	$51.2 \pm 0.2$	$51.3 \pm 0.2$	$51.6 \pm 0.2$
15	No-irradiated	$51.3 \pm 0.2$	$51.1 \pm 0.2$	$50.8 \pm 0.1$	$51.0 \pm 0.2$	$50.8 \pm 0.2$	$50.9 \pm 0.1$	$51.0 \pm 0.1$	$51.3 \pm 0.1$
10	No-irradiated	$51.0 \pm 0.2$	$50.8\pm~0.1$	$50.5 \pm 0.1$	$50.7 \pm 0.2$	$50.5 \pm 0.2$	$50.7 \pm 0.2$	$50.8 \pm 0.2$	$51.1 \pm 0.2$
0	No-irradiated	$50.4 \pm 0.1$	$50.3 \pm 0.1$	$50.0 \pm 0.2$	$50.1 \pm 0.1$	$50.0 \pm 0.3$	$50.1 \pm 0.1$	$50.2 \pm 0.1$	$50.5 \pm 0.1$
-10	No-irradiated	$49.8 \pm 0.1$	$49.7 \pm 0.1$	$49.4 \pm 0.1$	$49.6 \pm 0.1$	$49.4 \pm 0.3$	$49.5~\pm~0.1$	$49.6 \pm 0.2$	$49.9 \pm 0.1$
-20	No-irradiated	$49.3 \pm 0.1$	$49.2 \pm 0.1$	$48.8 \pm 0.1$	$49.0 \pm 0.2$	$48.9 \pm 0.2$	$49.0~\pm~0.1$	$49.1~\pm~~0.1$	$49.4 \pm 0.1$
-30	No-irradiated	$48.7 \pm 0.1$	$48.6 \pm 0.1$	$48.3 \pm 0.1$	$48.4 \pm 0.2$	$48.3 \pm 0.1$	$48.4 \pm 0.2$	$48.5 \pm 0.1$	$48.8 \pm 0.1$
-35	No-irradiated	$48.4 \pm 0.1$	$48.3 \pm 0.2$	$48.0 \pm 0.2$	$48.2 \pm 0.2$	$48.0~\pm~0.4$	$48.1 \pm 0.2$	$48.2 \pm 0.2$	$48.5\pm~0.1$
-40-A	No-irradiated	$49.1 \pm 6.9$	$49.0 \pm 6.3$	$47.8 \pm 0.3$	$49.2 \pm 7.0$	$48.9~\pm~~5.7$	$49.1 \pm 6.4$	$48.0 \pm 0.1$	$48.2 \pm 0.2$
-40-B	No-irradiated	$48.3 \pm 4.4$	$48.0 \pm 0.1$	$49.2 \pm 2.7$	$47.9 \pm 0.2$	$48.9 \pm  3.6$	$49.3 \pm  5.8$	$49.3 \pm  5.5$	$49.2 \pm 8.2$
-40-C	No-irradiated	$48.2 \pm 0.1$	$49.1 \pm 7.5$	$49.2 \pm 2.8$	$49.2 \pm 7.3$	$49.1 \pm 2.7$	$48.3 \pm 17.9$	$49.2 \pm 6.8$	$49.2 \pm 7.0$
-40-D	No-irradiated	±	±	±	±	±	±	±	±

- Breakdown voltages for all modules at temperatures between 20 °C to -35 °C are fine.
- For all modules instead of #4 and #5, we are able to identify meaningful fit at -40 °C (green)
- For modules #4 and #5, it looks the data files -40-D is missing in database, right?